

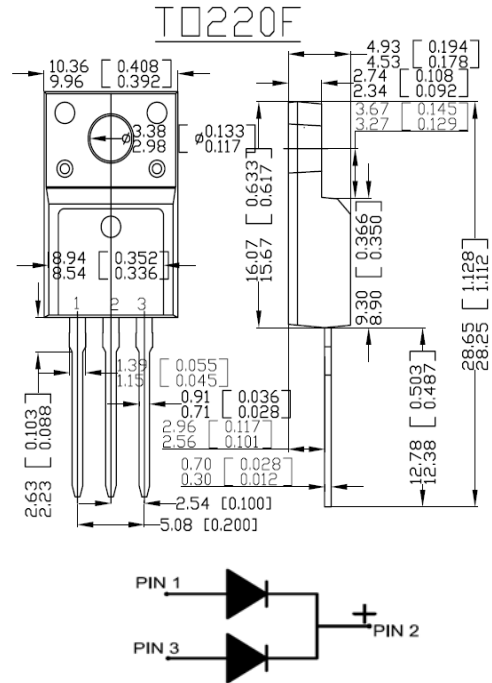


TO- 220F SCHOTTKY BARRIER RECTIFIERS

MBR20150

FEATURES

- Schottky Barrier Chip
- Guard Ring Die Construction for Transient Protection
- Low Power Loss,High Efficiency
- High Surge Capability
- High Current Capability and Low Forward Voltage Drop
- For Use in Low Voltage,High Frequency Inverters,Free Wheeling,and Polarity Protection Applications



Dimensions in millimeters and (inches)

ELECTRICAL CHARACTERISTICS (Tamb=25°C)

Characteristic	Symbol	MBR20150	Unit
Peak Repetitive Reverse Voltage	V_{RRM}	150	V
Working Peak Reverse Voltage	V_{RWM}		
DC Blocking Voltage	V_R		
Average Rectified Output Current	I_C	20	A
Maximum Instantaneous Forward Voltage	V_F	@ $I_F = 10A, T_c = 25^\circ C$	0.85
		@ $I_F = 10A, T_c = 125^\circ C$	0.82
		@ $I_F = 20A, T_c = 25^\circ C$	0.95
		@ $I_F = 20A, T_c = 125^\circ C$	0.85
Peak Reverse Current @ $T_c = 25^\circ C$ at Rated DC Blocking Voltage @ $T_c = 125^\circ C$	I_R	50 200	μA
Operating and Storage Temperature Range	T_j, T_{stg}	-55 to +150	$^\circ C$

Fig. 1: Average forward power dissipation versus average forward current (per diode).

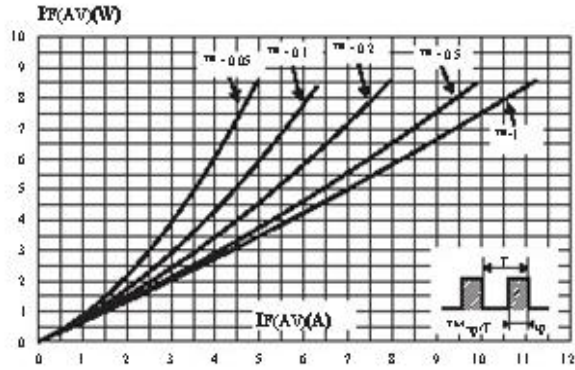


Fig. 2: Average forward current versus ambient temperature ($\delta = 0.5$, per diode).

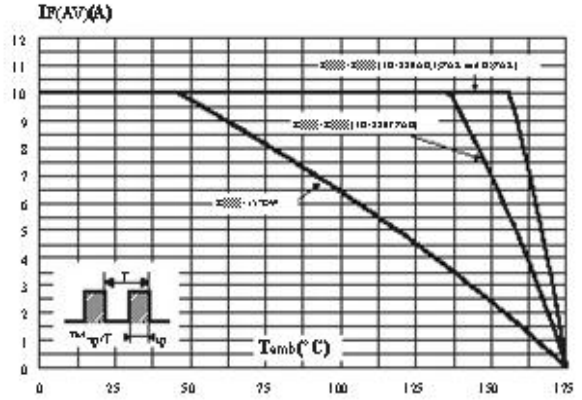


Fig. 3: Junction capacitance versus reverse voltage applied (typical values, per diode).

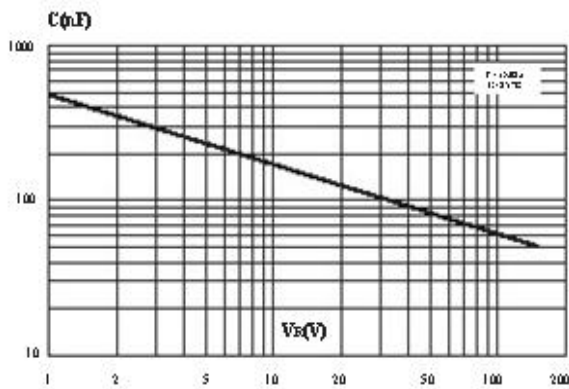


Fig. 4: Normalized avalanche power derating versus junction temperature.

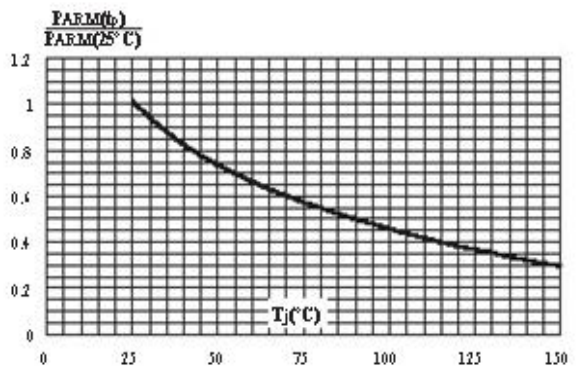


Fig. 5: Reverse leakage current versus reverse voltage applied (typical values, per diode).

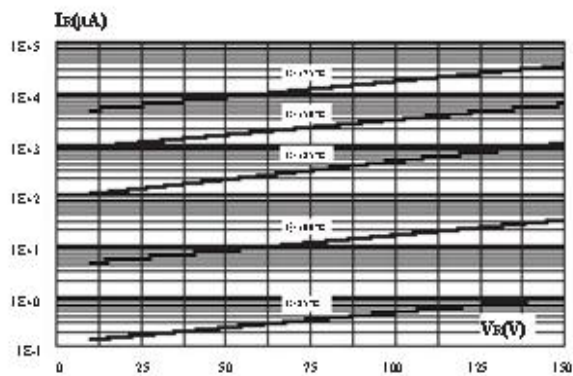


Fig. 6: Non repetitive surge peak forward current versus overload duration (maximum values, per diode).

